

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (L²-π-MOS V)

2SK2232

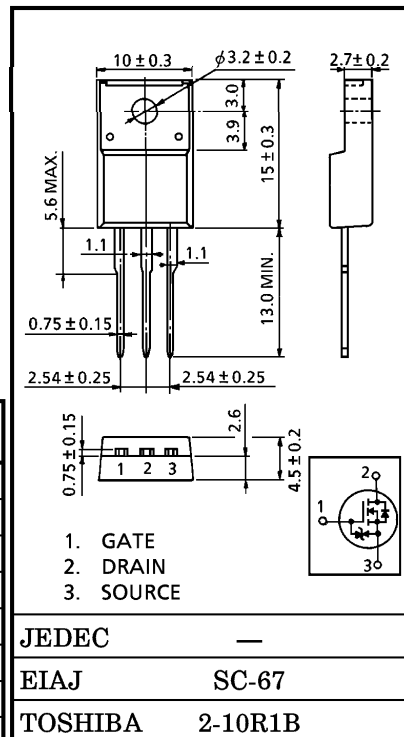
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS
 CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS
 Unit in mm

- 4V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 36m\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 16S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 60V$)
- Enhancement-Mode : $V_{th} = 0.8 \sim 2.0V$ ($V_{DS} = 10V, I_D = 1mA$)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current	DC	I_D	25
	Pulse	I_{DP}	100
Drain Power Dissipation (Tc = 25°C)	P_D	35	W
Single Pulse Avalanche Energy**	E_{AS}	156	mJ
Avalanche Current	I_{AR}	25	A
Repetitive Avalanche Energy*	E_{AR}	3.5	mJ
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



Weight : 1.9g

HERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel To Case	$R_{th(ch-c)}$	3.57	°C/W
Thermal Resistance, Channel To Ambient	$R_{th(ch-a)}$	62.5	°C/W

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 25V$, Starting $T_{ch} = 25°C$, $L = 339\mu H$, $R_G = 25\Omega$, $I_{AR} = 25A$

This transistor is an electrostatic sensitive device. Please handle with caution.

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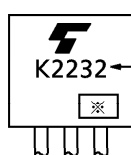
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	VGS = ±16V, VDS = 0V	—	—	±10	μA
Drain Cut-off Current		IDSS	VDS = 60V, VGS = 0V	—	—	100	μA
Drain-Source Breakdown Voltage		V (BR) DSS	ID = 10mA, VGS = 0V	60	—	—	V
Gate Threshold Voltage		Vth	VDS = 10V, ID = 1mA	0.8	—	2.0	V
Drain-Source ON Resistance		RDS (ON)	VGS = 4V, ID = 12A	—	0.057	0.08	Ω
			VGS = 10V, ID = 12A	—	0.036	0.046	
Forward Transfer Admittance		Yfs	VDS = 10V, ID = 12A	10	16	—	S
Input Capacitance		Ciss	VDS = 10V, VGS = 0V f = 1MHz	—	1000	—	pF
Reverse Transfer Capacitance		Crss		—	200	—	
Output Capacitance		Coss		—	550	—	
Switching Time	Rise Time	tr		—	20	—	ns
	Turn-on Time	ton		—	30	—	
	Fall Time	tf		—	55	—	
	Turn-off Time	toff		VIN : tr, tf < 5ns Duty ≤ 1%, tw = 10μs	—	130	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Qg	VDD ≐ 48V, VGS = 10V ID = 25A	—	38	—	nC
Gate-Source Charge		Qgs		—	25	—	
Gate-Drain ("Miller") Charge		Qgd		—	13	—	

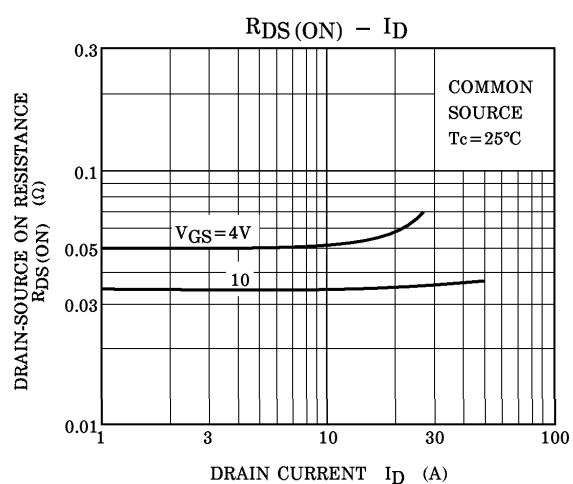
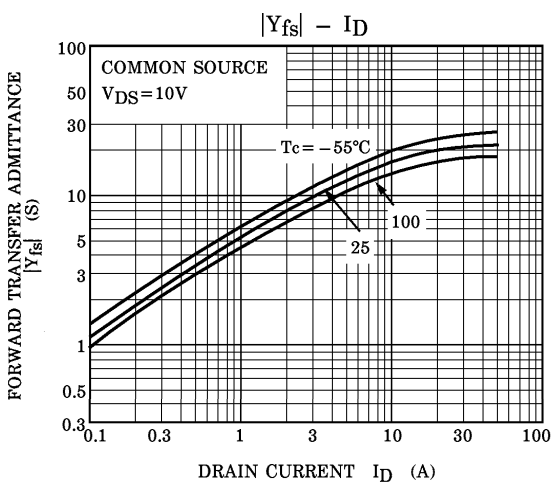
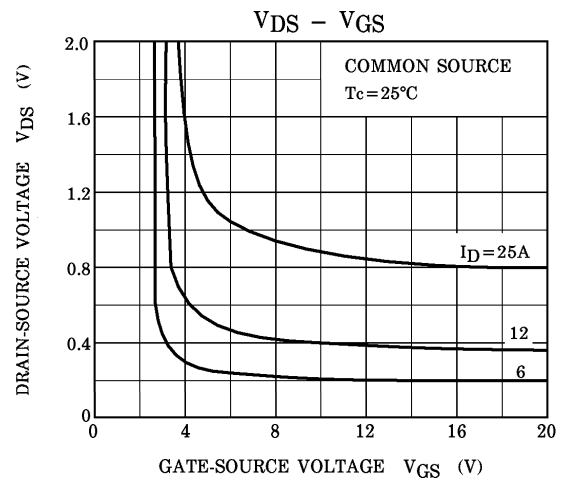
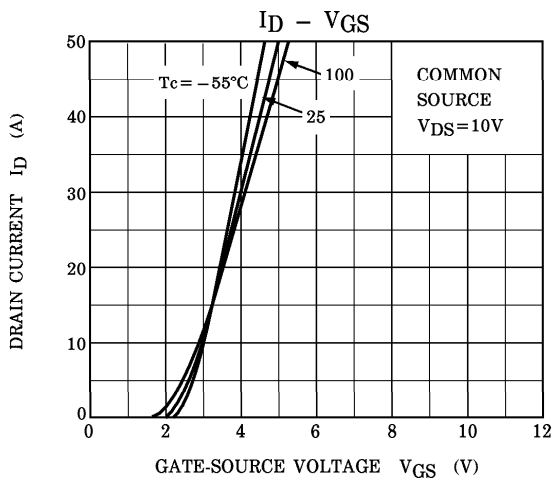
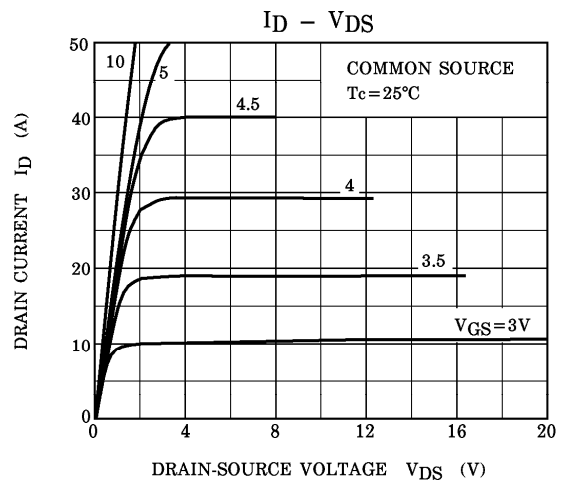
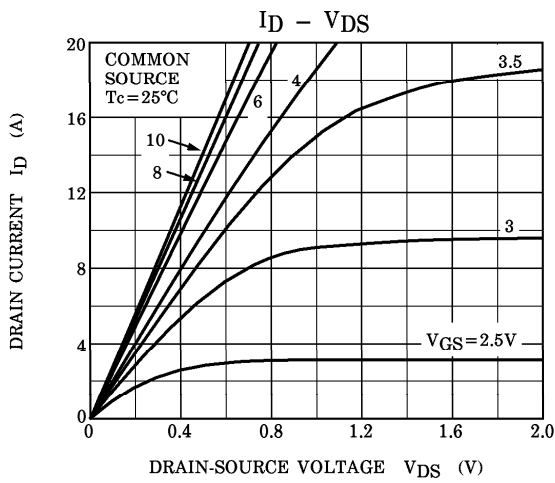
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

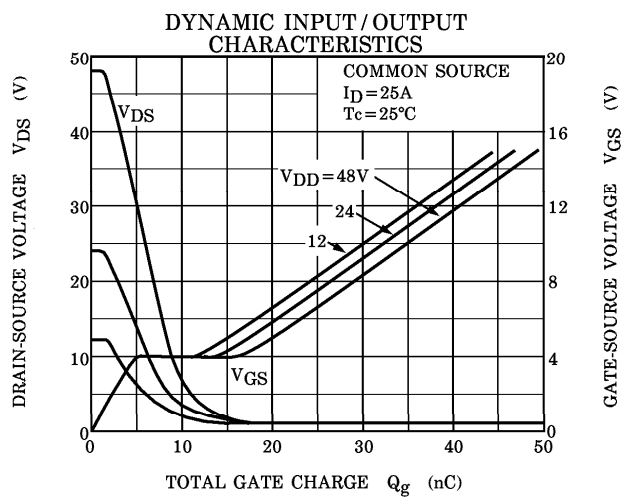
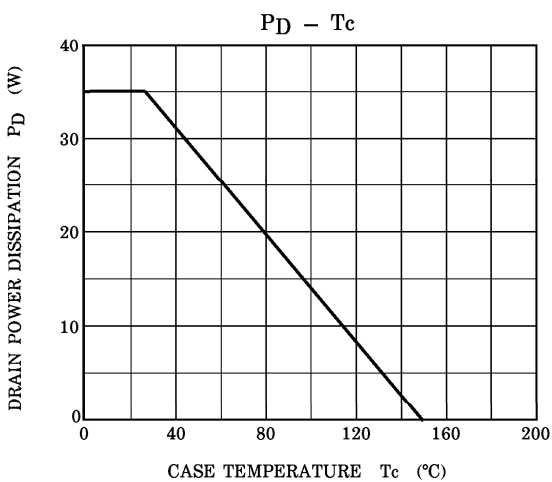
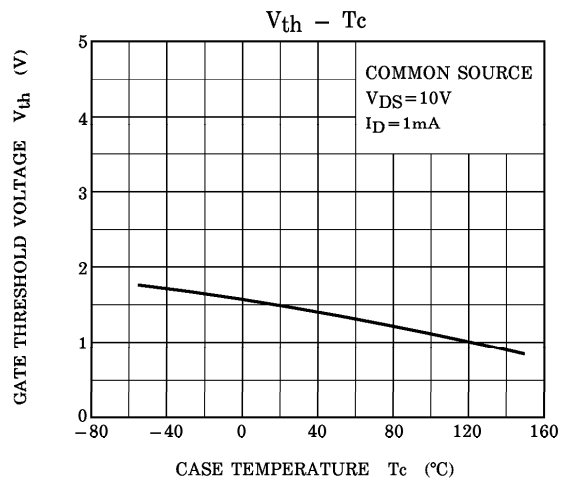
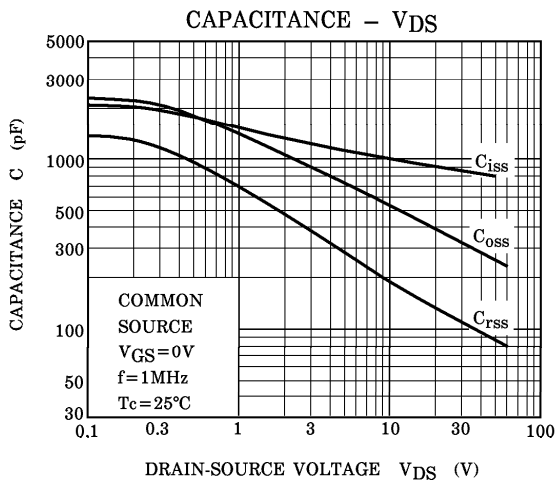
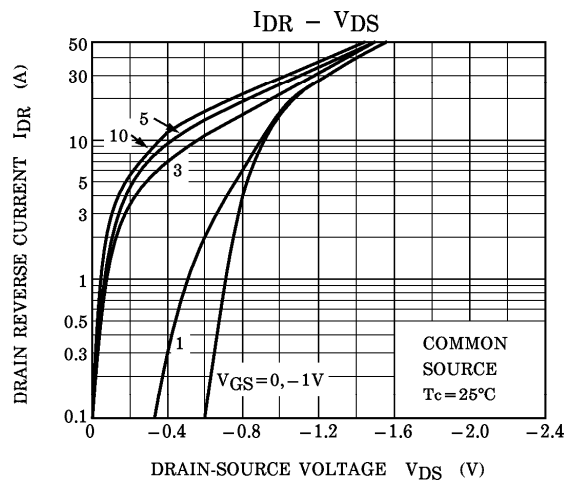
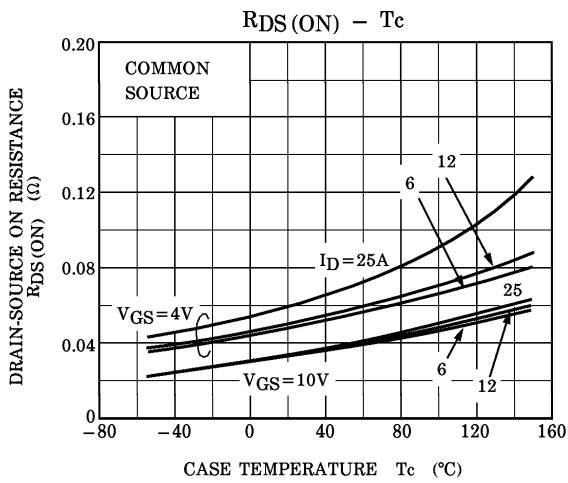
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	IDR	—	—	—	25	A
Pulse Drain Reverse Current	IDRP	—	—	—	100	A
Diode Forward Voltage	VDSF	IDR = 25A, VGS = 0V	—	—	-1.8	V
Reverse Recovery Time	trr	IDR = 25A, VGS = 0V	—	50	—	ns
Reverse Recovery Charge	Qrr	dIDR / dt = 50A / μs	—	35	—	nC

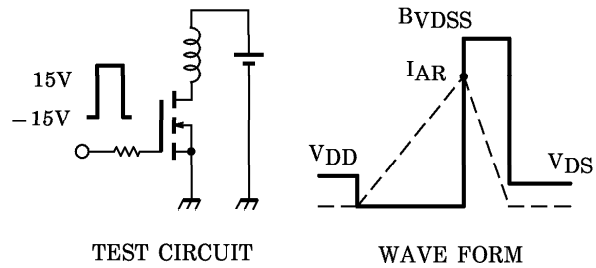
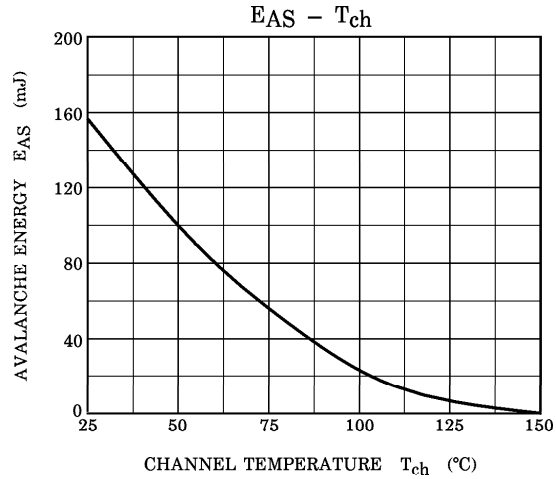
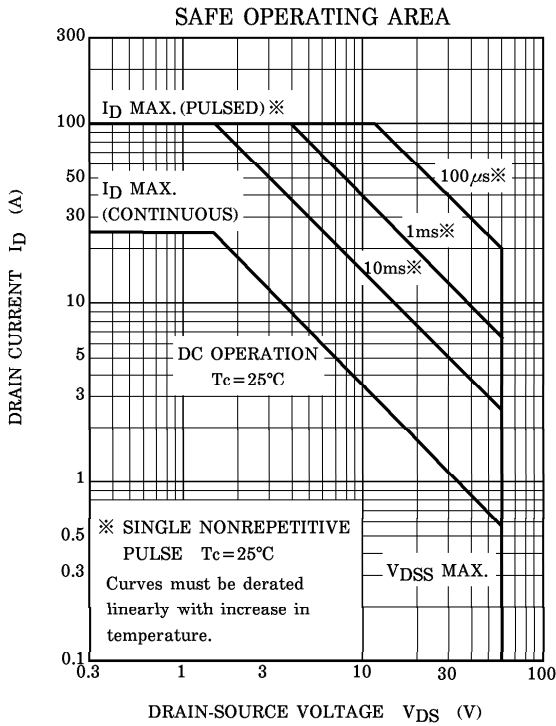
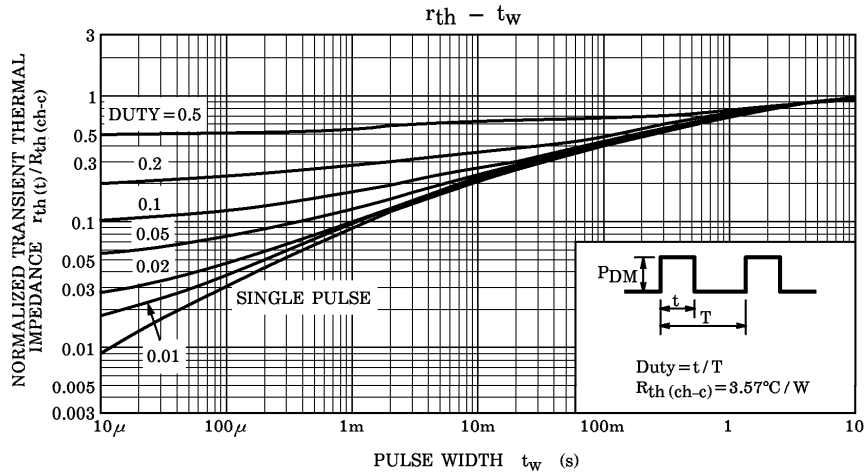
MARKING



TYPE ← K2232
 ※ Lot Number
 □ □ — Month (Starting from Alphabet A)
 — Year (Last Number of the Christian Era)







Peak $I_{AR} = 25A$, $R_G = 25\Omega$
 $V_{DD} = 25V$, $L = 339\mu H$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$